TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VHCT574AF,TC74VHCT574AFT,TC74VHCT574AFK

Octal D-Type Flip-Flop with 3-State Output

The TC74VHCT574A is an advanced high speed CMOS OCTAL FLIP-FLOP with 3-STATE OUTPUT fabricated with silicon gate C²MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

This 8-bit D-type flip-flop is controlled by a clock input (CK) and an output enable input (\overline{OE}).

When the \overline{OE} input is high, the eight outputs are in a high impedance state.

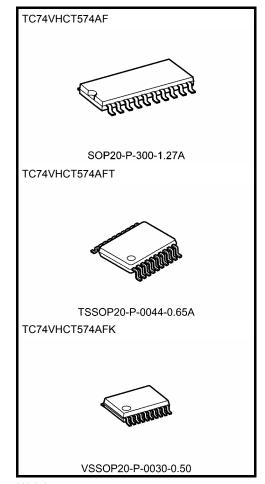
The input voltage are compatible with TTL output voltage. This device may be used as a level converter for interfacing $3.3\ V$ to $5\ V$ system.

Input protection and output circuit ensure that 0 to 5.5 V can be applied to the input and output $^{\rm (Note)}$ pins without regard to the supply voltage. These structure prevents device destruction due to mismatched supply and input/output voltages such as battery back up, hot board insertion, etc.

Note: Output in off-state

Features

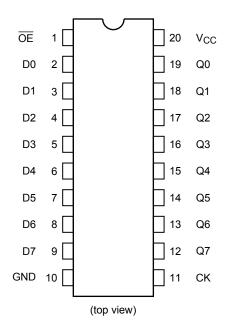
- High speed: $f_{max} = 140 \text{ MHz}$ (typ.) at $V_{CC} = 5 \text{ V}$
- Low power dissipation: $I_{CC} = 4 \mu A \text{ (max)}$ at $T_{a} = 25 \text{°C}$
- Compatible with TTL outputs: $V_{IL} = 0.8 \text{ V (max)}$ $V_{IH} = 2.0 \text{ V (min)}$
- Power down protection is provided on all inputs and outputs.
- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Low noise: VOLP = 1.6 V (max)
- Pin and function compatible with the 74 series (74AC/HC/F/ALS/LS etc.) 574 type.



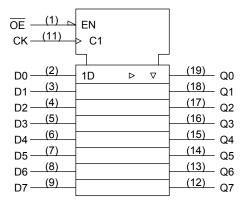
Weight

SOP20-P-300-1.27A : 0.22 g (typ.) TSSOP20-P-0044-0.65A : 0.08 g (typ.) VSSOP20-P-0030-0.50 : 0.03 g (typ.)

Pin Assignment



IEC Logic Symbol



Truth Table

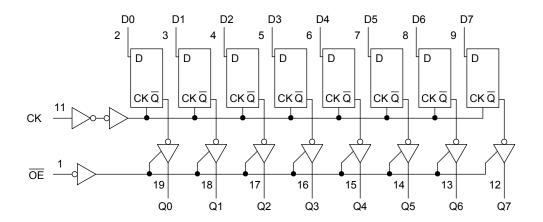
	Inputs	Output	
ŌĒ	CK	D	Output
Н	Х	Х	Z
L	\neg	Х	Qn
L		L	L
L		Н	Н

X: Don't care

Z: High impedance

Q_n: No change

System Diagram





Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	−0.5 to 7.0	V
DC input voltage	V _{IN}	−0.5 to 7.0	V
DC output voltage	V	-0.5 to 7.0 (Note 2)	V
DC output voltage	Vout	-0.5 to V _{CC} + 0.5 (Note 3)	V
Input diode current	lik	-20	mA
Output diode current	I _{OK}	±20 (Note 4)	mA
DC output current	I _{OUT}	±25	mA
DC V _{CC} /ground current	Icc	±75	mA
Power dissipation	P_{D}	180	mW
Storage temperature	T _{stg}	−65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: Output in off-state

Note 3: High or low state. IOUT absolute maximum rating must be observed.

Note 4: Vout < GND, Vout > Vcc

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	4.5 to 5.5	V
Input voltage	V _{IN}	0 to 5.5	V
Output voltage	V	0 to 5.5 (Note 2)	V
Output voltage	V _{OUT}	0 to V _{CC} (Note 3)	V
Operating temperature	T _{opr}	−40 to 85	°C
Input rise and fall time	dt/dV	0 to 20	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either V_{CC} or GND.

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Note 2: $V_{CC} = 0 V$

Note 3: High or low state



Electrical Characteristics

DC Characteristics

Characteristics	Symbol	Test Condition		Ta = 25°C			Ta = -40 to 85°C		Unit	
				V _{CC} (V)	Min	Тур.	Max	Min	Max	
High-level input voltage	V _{IH}	_		4.5 to 5.5	2.0	_	_	2.0	_	V
Low-level input voltage	V _{IL}		_	4.5 to 5.5	_	_	0.8	_	0.8	V
High-level output	V	V _{IN}	I _{OH} = -50 μA	4.5	4.40	4.50	-	4.40	_	V
voltage	V _{OH}	= V _{IH} or V _{IL}	I _{OH} = -8 mA	4.5	3.94	_	_	3.80	_	
Low-level output		V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50 μA	4.5	_	0.0	0.10	_	0.10	V
voltage	V_{OL}		I _{OL} = 8 mA	4.5	_	_	0.36	_	0.44	
3-state output off-state current	I _{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND		5.5	_	_	±0.25	_	±2.50	μА
Input leakage current	I _{IN}	V _{IN} = 5.5 V or GND		0 to 5.5	_	_	±0.1	_	±1.0	μΑ
	Icc	V _{IN} = V _{CC} or GND		5.5	1	_	4.0	ı	40.0	μA
Quiescent supply current	Ісст	Per input: V _{IN} = 3.4 V Other input: V _{CC} or GND		5.5	_	_	1.35	_	1.50	mA
Output leakage current	I _{OPD}	V _{OUT} = 5	5.5 V	0		_	+0.5		+5.0	μΑ

Timing Requirements (input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition		Ta = 25°C		Ta = -40 to 85°C	Unit
			V _{CC} (V)	Тур.	Limit	Limit	
Minimum pulse width (CK)	t _{w (H)}	_	5.0 ± 0.5	_	6.5	8.5	ns
Minimum set-up time	t _s	_	5.0 ± 0.5	_	2.5	2.5	ns
Minimum hold time	t _h	_	5.0 ± 0.5	_	2.5	2.5	ns

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AC Characteristics (input: $t_r = t_f = 3$ ns)

Characteristics	Tes Symbol .		st Condition		Ta = 25°C			Ta = -40 to 85°C		Unit
	,		V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	
Propagation delay time	t _{pLH}	_	5.0 ± 0.5	15	_	4.1	9.4	1.0	10.5	ns
(CK-Q)	t_{pHL}		0.0 _ 0.0	50	_	5.6	10.4	1.0	11.5	113
3-state output enable	t_{pZL}	D 1 kO	50+05	15	_	6.5	10.2	1.0	11.5	ne
time	t _{pZH}	$R_L = 1 k\Omega$	5.0 ± 0.5	50	_	7.3	11.2	1.0	12.5	ns
3-state output disable time	t _{pLZ} t _{pHZ}	R _L = 1 kΩ	5.0 ± 0.5	50	_	7.0	11.2	1.0	12.0	ns
Maximum clock	f _{max}	_	5.0 ± 0.5	15	90	140	_	80	_	MHz
frequency				50	85	130	_	75	_	IVITZ
Output to output skew	t _{osLH}	(Note 1)	5.0 ± 0.5	50	_	_	1.0	_	1.0	ns
Input capacitance	C _{IN}		_		_	4	10	_	10	pF
Output capacitance	C _{OUT}		_		_	9	_	_	_	pF
Power dissipation capacitance	C _{PD}			(Note 2)	_	25	_	_	_	pF

Note 1: Parameter guaranteed by design.

$$t_{OSLH} = |t_{DLHm} - t_{DLHn}|, t_{OSHL} = |t_{DHLm} - t_{DHLn}|$$

Note 2: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 (per F/F)$$

And the total C_{PD} when n pcs. of latch operate can be gained by the following equation:

C_{PD} (total) = 14 + 11·n

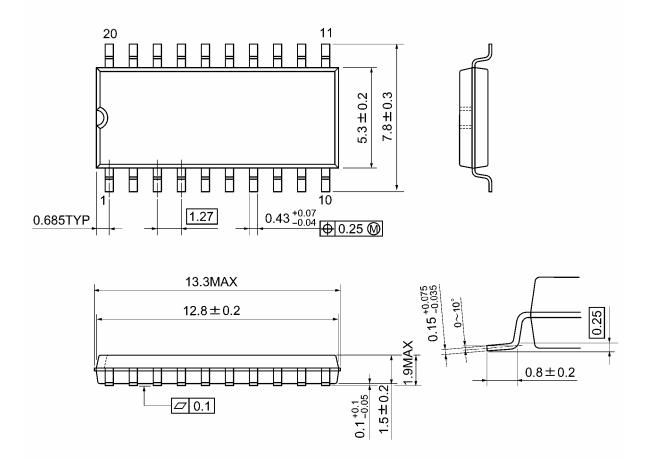
Noise Characteristics (input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition		Ta = 25°C		Unit
Characteristics	Symbol		V _{CC} (V)	Тур.	Max	Offic
Quiet output maximum dynamic V _{OL}	V_{OLP}	C _L = 50 pF	5.0	1.1	1.5	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	C _L = 50 pF	5.0	-1.1	-1.5	V
Minimum high level dynamic input voltage	V_{IHD}	C _L = 50 pF	5.0	_	2.0	V
Maximum low level dynamic input voltage	V _{ILD}	C _L = 50 pF	5.0	_	0.8	V

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Package Dimensions

SOP20-P-300-1.27A Unit: mm



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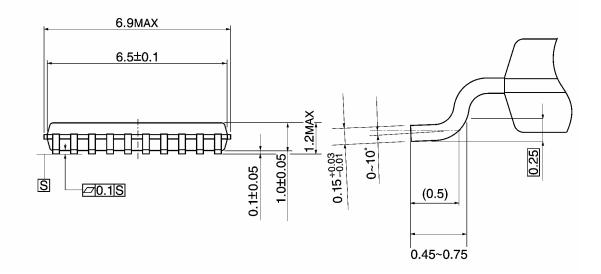
Weight: 0.22 g (typ.)



Package Dimensions

Unit: mm

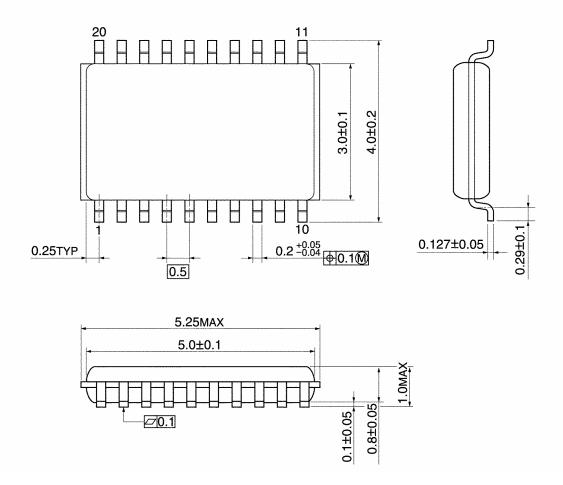
20
11
10
0.325TYP
0.65
0.22+0.09
10
0.22+0.09



Weight: 0.08 g (typ.)

Package Dimensions

VSSOP20-P-0030-0.50 Unit: mm



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Weight: 0.03 g (typ.)

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20070701-EN GENERAL

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